

Zhizhong Yuan

List of Publications by Year in descending order

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13
papers

551
citations

933447

10
h-index

1125743

13
g-index

15
all docs

15
docs citations

15
times ranked

715
citing authors

#	ARTICLE	IF	CITATIONS
1	Enhancement of ZnO light emission via coupling with localized surface plasmon of Ag island film. Applied Physics Letters, 2008, 92, .	3.3	156
2	Photoluminescence of Si-rich silicon nitride: Defect-related states and silicon nanoclusters. Applied Physics Letters, 2007, 90, 131903.	3.3	124
3	Silicon Nanocrystals as an Enabling Material for Silicon Photonics. Proceedings of the IEEE, 2009, 97, 1250-1268.	21.3	74
4	Electroluminescence of SnO ₂ /p-Si heterojunction. Applied Physics Letters, 2008, 92, .	3.3	55
5	Correlation between luminescence and structural evolution of Si-rich silicon oxide film annealed at different temperatures. Journal of Applied Physics, 2007, 101, 103504.	2.5	29
6	Photoluminescence of Tb ³⁺ doped SiN _x films grown by plasma-enhanced chemical vapor deposition. Journal of Applied Physics, 2006, 100, 083106.	2.5	25
7	High-cycle fatigue behavior of high-nitrogen austenitic stainless steel. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2009, 517, 257-260.	5.6	25
8	Impact properties of high-nitrogen austenitic stainless steels. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2008, 475, 202-206.	5.6	24
9	Enhanced photoluminescence of Tb ³⁺ in SnO ₂ film by phosphorus diffusion process. Journal of Alloys and Compounds, 2009, 474, 246-249.	5.5	11
10	Deformation microstructures of austenitic stainless steel 2Cr13Mn9Ni4 under ultrafast strain rate by laser shock processing. Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing, 2013, 587, 244-249.	5.6	11
11	Photoluminescence of Tb ³⁺ -doped SiN _x films with different Si concentrations. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 126-130.	3.5	6
12	Effects of defect, carrier concentration and annealing process on the photoluminescence of silicon pn diodes. Materials Science in Semiconductor Processing, 2007, 10, 173-178.	4.0	4
13	Electron-beam-induced current evidence for room-temperature photoluminescence of silicon pn diode. Vacuum, 2008, 82, 1337-1340.	3.5	3